

# [METHOD OF FORMING A FUSE]

## Abstract of Disclosure

A surface of a semiconductor substrate defined with at least one fuse area and at least one bonding pad area. A conductive layer with a thickness of  $12\text{k}\text{\AA}$  and a protective layer are sequentially formed on the surface of the semiconductor substrate. Then portions of the protective layer and portions of the conductive layer in the fuse area are etched to make the thickness for the remaining conductive layer in the fuse area be approximately  $5\text{k}\text{\AA}$ . Finally a dielectric layer is formed on the surface of the semiconductor substrate, and portions of the first dielectric layer and portions of the protective layer in the bonding pad area are etched until reaching the top surface of the conductive layer.

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## Figures

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